



BUK7675-55A

N-channel TrenchMOS standard level FET

25 August 2014

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _J ≥ 25 °C; T _J ≤ 175 °C		-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2 ; Fig. 3		-	-	20.3	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1		-	-	62	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _J = 175 °C; Fig. 11 ; Fig. 12		-	-	150	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _J = 25 °C; Fig. 11 ; Fig. 12		-	64	75	mΩ
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 11 A; V _{sup} ≤ 55 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{J(init)} = 25 °C; unclamped		-	-	30.3	mJ

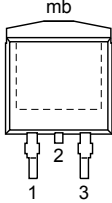
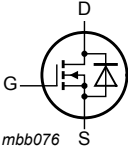


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404)	 mbb076
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7675-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7675-55A	BUK7675-55A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-20	20	V
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 1	-	62	W
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 2 ; Fig. 3	-	20.3	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 2	-	14.3	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 3	-	81	A
T_{stg}	storage temperature		-55	175	$^{\circ}\text{C}$
T_j	junction temperature		-55	175	$^{\circ}\text{C}$

Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$		-	20.3	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$		-	81	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 11\text{ A}$; $V_{sup} \leq 55\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; unclamped		-	30.3	mJ

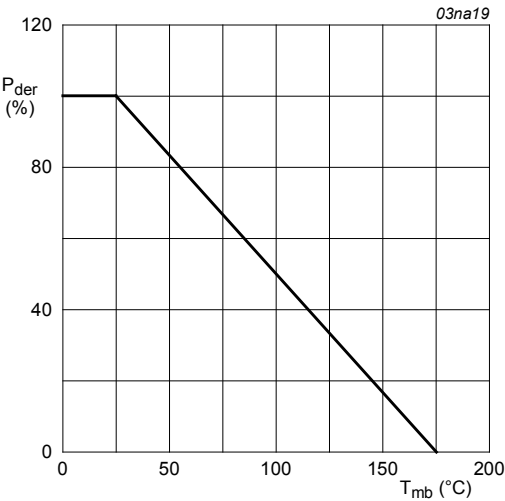


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

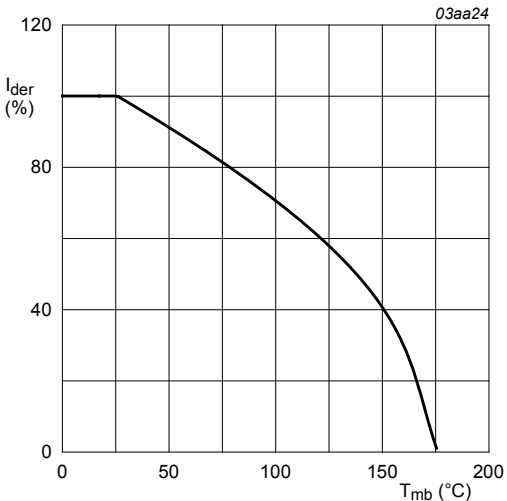


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

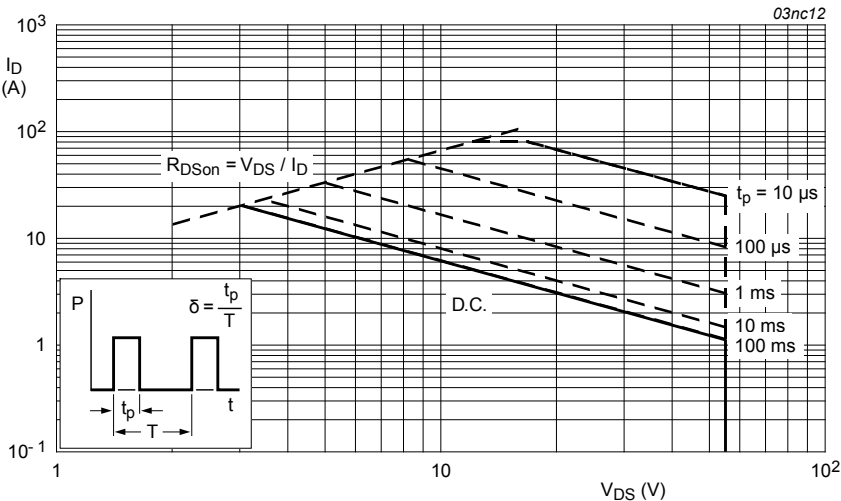


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25^{\circ}\text{C}; I_{DM} \text{ is single pulse}$$

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W

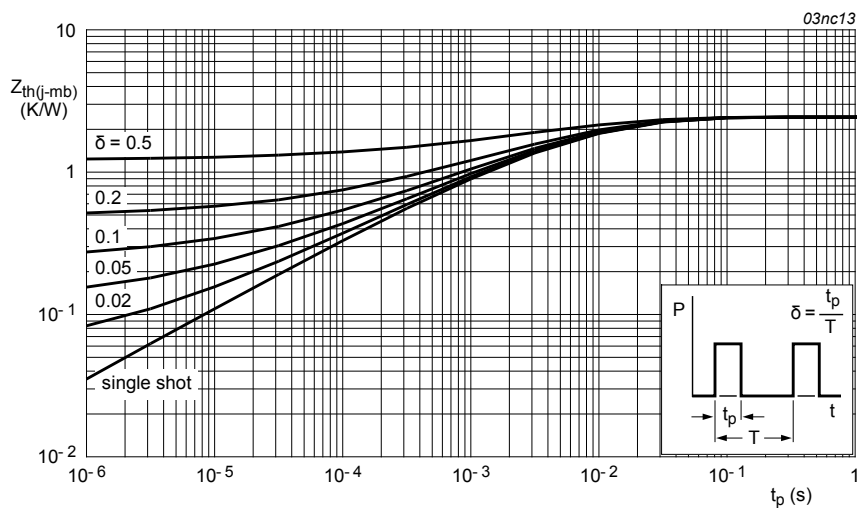


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_J = 25^\circ \text{C}$	55	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_J = -55^\circ \text{C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 175^\circ \text{C};$ Fig. 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = 25^\circ \text{C};$ Fig. 10	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_J = -55^\circ \text{C};$ Fig. 10	-	-	4.4	V
I_{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 175^\circ \text{C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_J = 25^\circ \text{C}$	-	0.05	10	μA

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12		-	-	150	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11; Fig. 12		-	64	75	mΩ
Dynamic characteristics							
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; Fig. 13		-	320	483	pF
C _{oss}	output capacitance			-	92	113	pF
C _{rss}	reverse transfer capacitance			-	64	90	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; R _{G(ext)} = 10 Ω; T _j = 25 °C		-	10	-	ns
t _r	rise time			-	50	-	ns
t _{d(off)}	turn-off delay time			-	70	-	ns
t _f	fall time			-	40	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; T _j = 25 °C		-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; T _j = 25 °C		-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; T _j = 25 °C		-	7.5	-	nH
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 14		-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C		-	32	-	ns
Q _r	recovered charge			-	120	-	nC

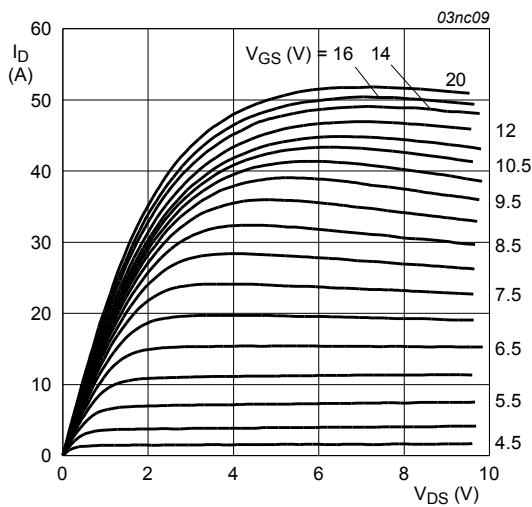


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25^\circ\text{C}$

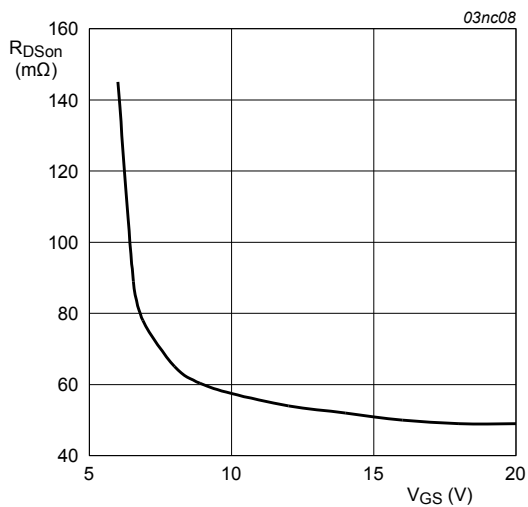


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}; I_D = 10\text{A}$

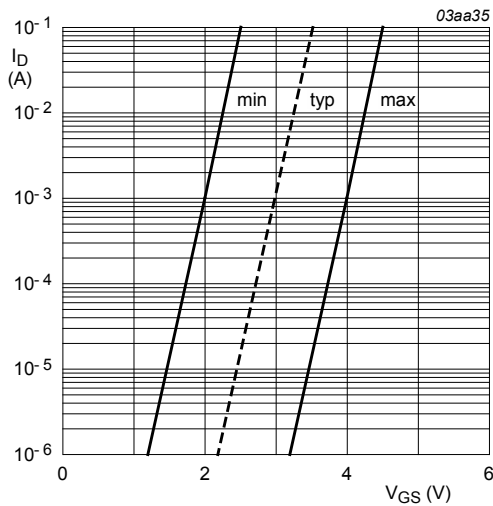


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

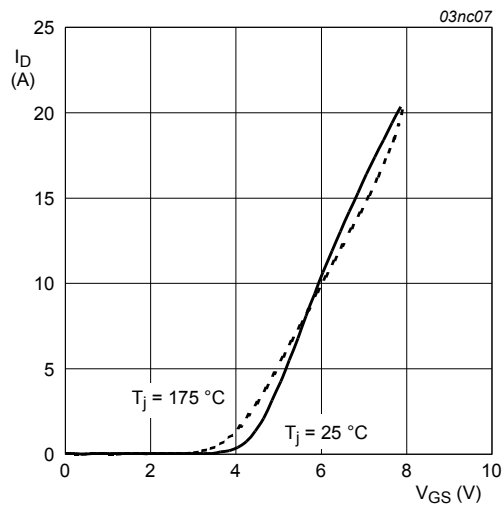


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$V_{DS} = 25\text{V}$

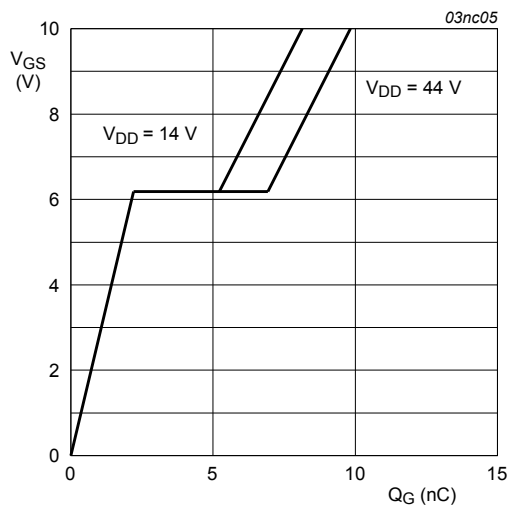


Fig. 9. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}\text{C}; I_D = 10\text{A}$$

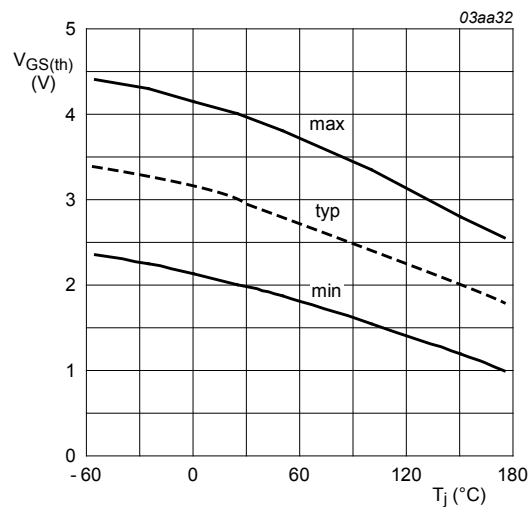


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1\text{mA}; V_{DS} = V_{GS}$$

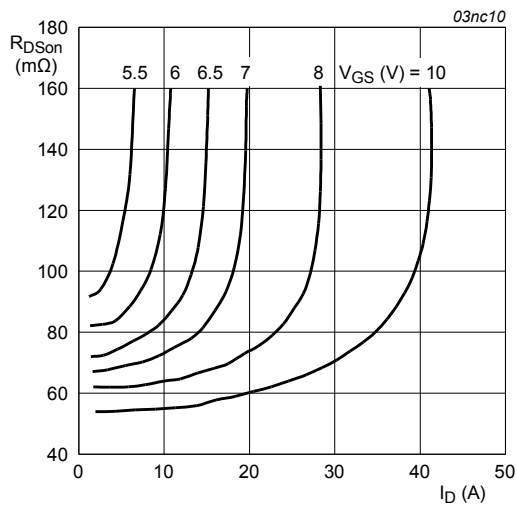


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}\text{C}$$

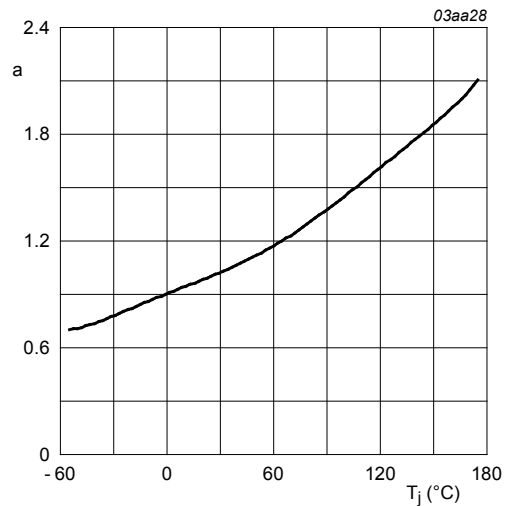


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

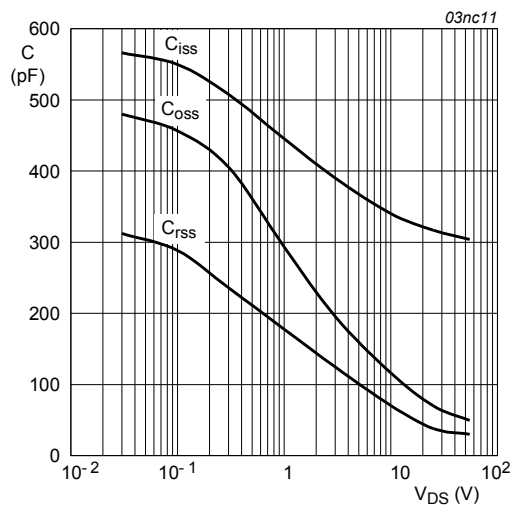


Fig. 13. Input, output and reverse capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0V; f = 1MHz$

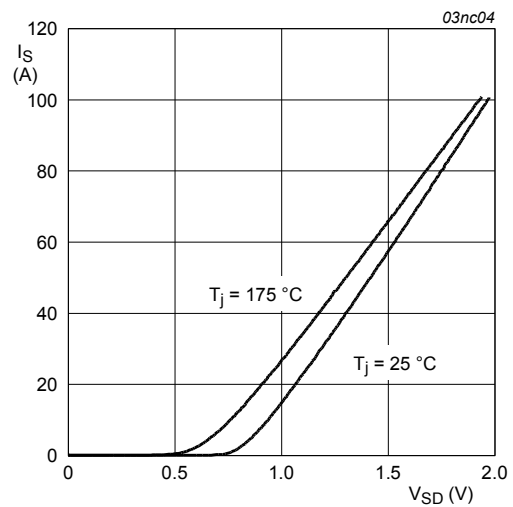


Fig. 14. Reverse diode current as a function of reverse diode voltage; typical values

$V_{GS} = 0V$

11. Package outline

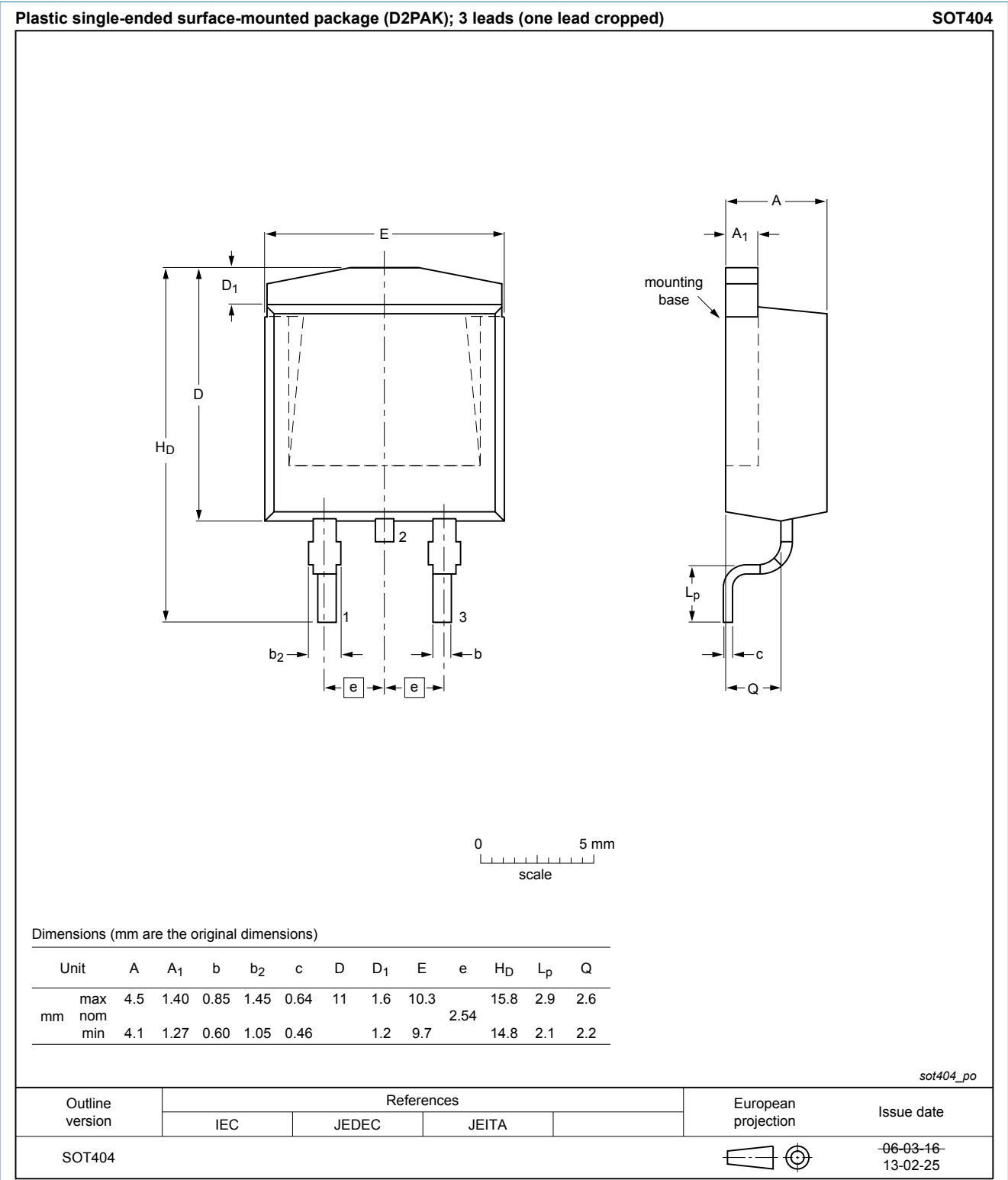


Fig. 15. Package outline D2PAK (SOT404)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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